# ne<mark>x</mark>peria

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In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

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Should be replaced with:

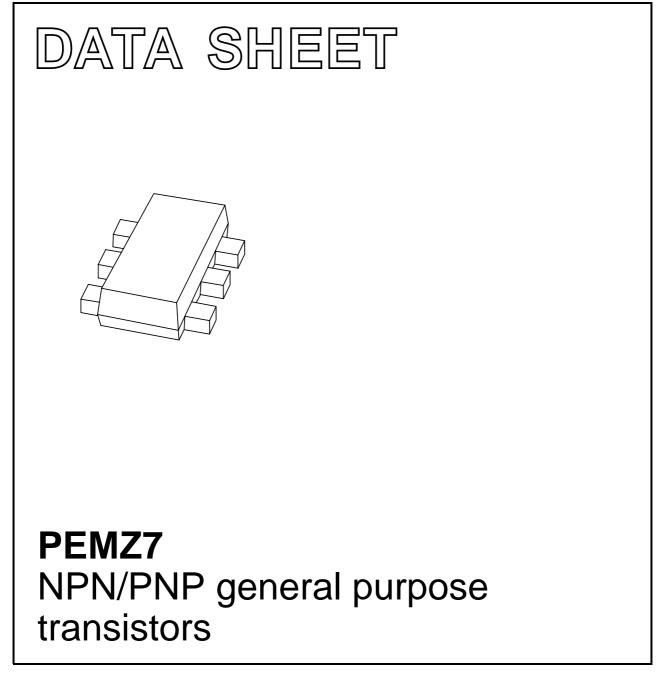
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

## DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2001 Sep 25 2001 Nov 07



#### FEATURES

- 300 mW total power dissipation
- Very small  $1.6 \times 1.2$  mm ultra thin package
- Self alignment during soldering due to straight leads
- Low collector capacitance
- Low V<sub>CEsat</sub>
- High current capabilities
- · Improved thermal behaviour due to flat leads
- Reduced required PCB area
- Reduced pick and place costs.

#### APPLICATIONS

- Heavy duty battery powered equipment (automotive, telecom and audio-video) such as motor and lamp drivers
- V<sub>CEsat</sub> critical applications such as latest low supply voltage IC applications
- All battery driven equipment, to save battery power.

#### DESCRIPTION

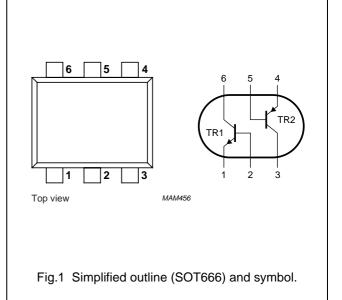
NPN/PNP low  $V_{\mbox{CEsat}}$  transistor pair in a SOT666 plastic package.

#### MARKING

TYPE NUMBER	MARKING CODE			
PEMZ7	Z7			

#### PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



# PEMZ7

## PEMZ7

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity					
V <sub>CBO</sub>	collector-base voltage	open emitter	_	15	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	12	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current (DC)		-	500	mA
I <sub>CM</sub>	peak collector current		-	1	А
I <sub>BM</sub>	peak base current		-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C; note 1$	-	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
Per device	9	·			
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	-	300	mW

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

#### Notes

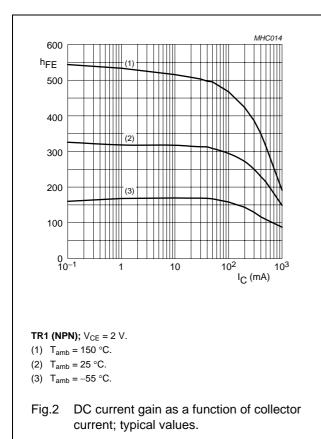
- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering method is reflow soldering.

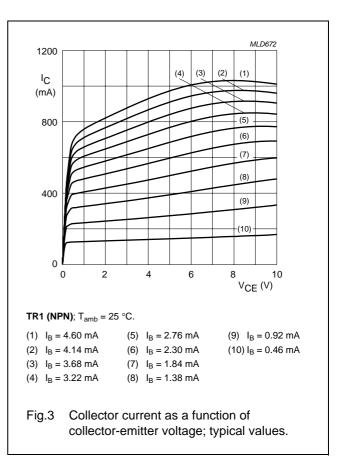
## PEMZ7

#### CHARACTERISTICS

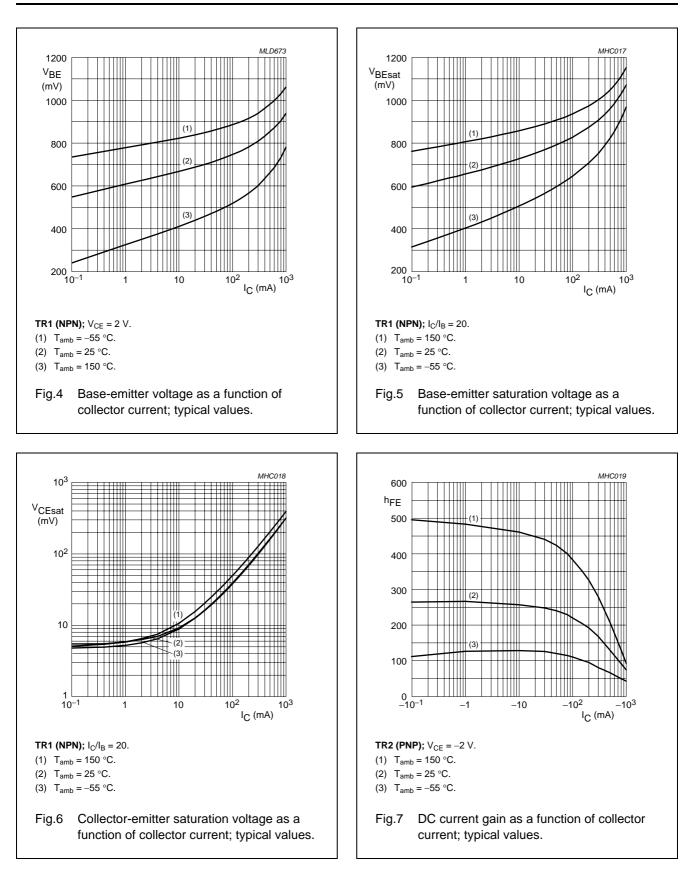
 $T_{amb} = 25 \ ^{\circ}C$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor; for the PNP transistor with negative polarity					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 15 \text{ V}; \text{ I}_{\text{E}} = 0$	-	_	100	nA
		V <sub>CB</sub> = 15 V; I <sub>E</sub> = 0; T <sub>j</sub> = 150 °C	-	_	50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 V; I_{C} = 0$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 10 mA	200	-	-	
V <sub>CEsat</sub>	collector-emitter saturation	I <sub>C</sub> = 200 mA; I <sub>B</sub> = 10 mA	-	-	220	mV
	voltage					
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 100 mA; V <sub>CE</sub> = 5 V;				
	TR1 (NPN)	f = 100 MHz	250	420	-	MHz
	TR2 (PNP)		100	280	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$				
	TR1 (NPN)		-	4.4	6	pF
	TR2 (PNP)		-	_	10	pF

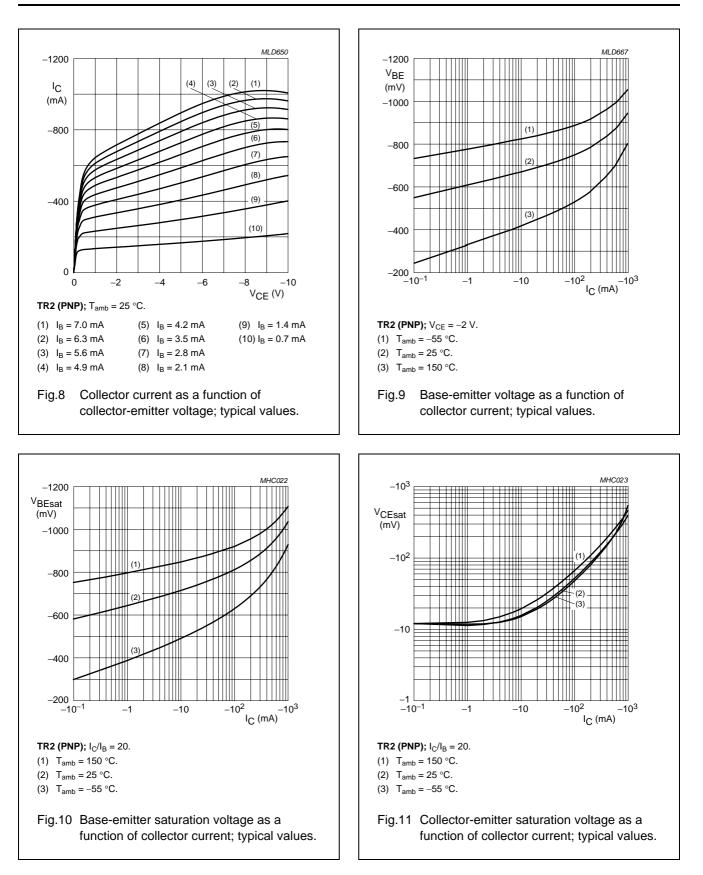




## PEMZ7



## PEMZ7

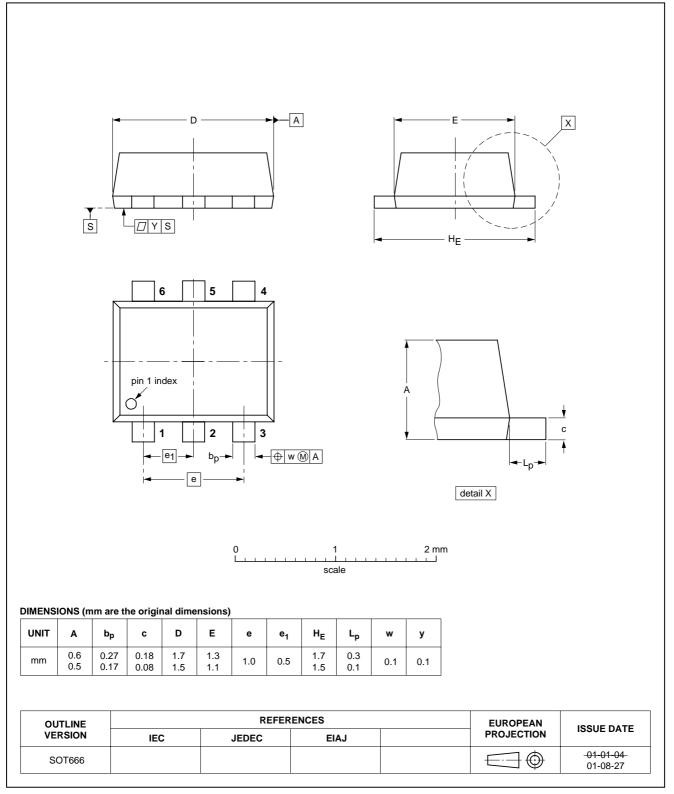


#### Product data sheet

## NPN/PNP general purpose transistors

#### PACKAGE OUTLINE





PEMZ7

**SOT666** 

PEMZ7

#### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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## **NXP Semiconductors**

#### **Customer notification**

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#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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